

Electronic supplementary information for: Why do Si quantum dots with a stronger short-lived component have lower external photoluminescence quantum yield?

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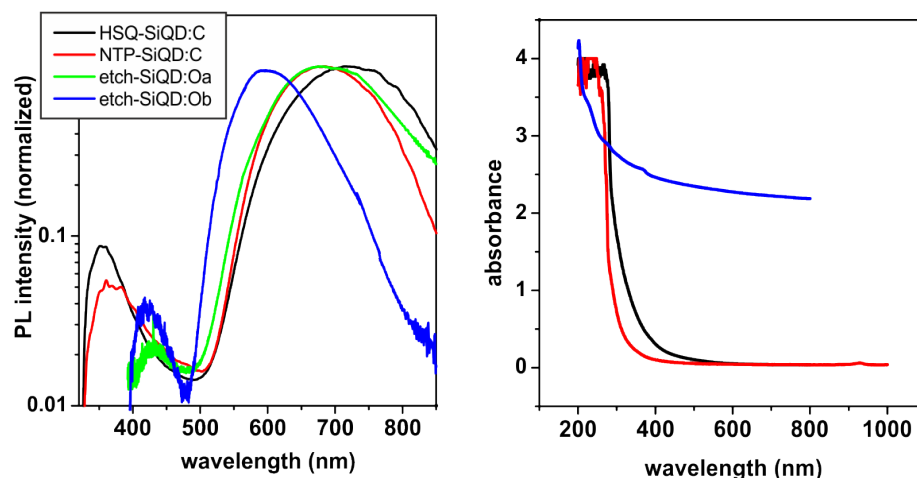


Fig. S1 Steady-state photoluminescence (left) and absorbance (right) of the studied samples under continuous 325 nm excitation. The absorbance was recalculated from transmittance measurements. Please note that larger agglomerates form in the oxidized sample (etch-SiQDs:Ob), which results in the background in the absorbance curve.

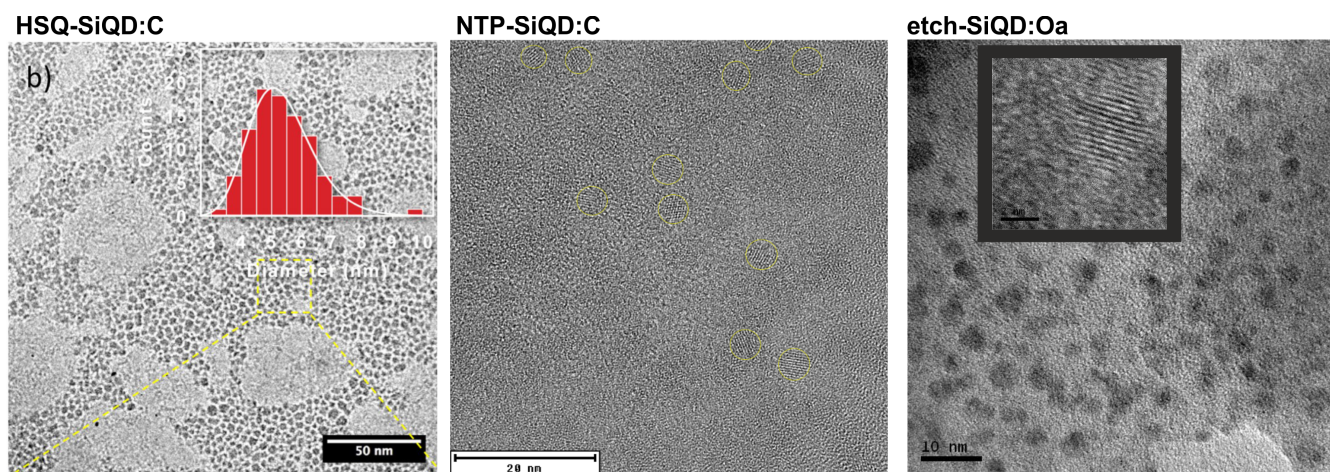


Fig. S2 HRTEMs of the studied SiQDs.

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